#### TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# **SM3GZ47**, **SM3JZ47**

#### AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage: VDRM = 400V, 600V
- R.M.S On-State Current: IT (RMS) = 3A
- High Commutating (dv / dt)
- Isolation Voltage: VISOL = 1500V AC

#### **ABSOLUTE MAXIMUM RATINGS**

CHARACTERIS	SYMBOL	RATING	THAU		
Repetitive Peak Off-State Voltage	SM3GZ47	V2211	400		
	SM3JZ47	$V_{DRM}$	600		
R.M.S On-State Current (Full Sine Waveform Tc =	I <sub>T (RMS)</sub>	3	A		
Peak One Cycle Surge On-State Current (Non-Repetitive)		ITSM	30 (50Hz)	> A	
		TISM	33 (60Hz)	> ^	
I <sup>2</sup> t Limit Value (t = 1~10n	I <sup>2</sup> t	4.5	A <sup>2</sup> s		
Critical Rate of Rise of O Current	di / dt	50	A / µs		
Peak Gate Power Dissipa	P <sub>GM</sub>	5	W		
Average Gate Power Dis	PG (AV)	0.5	_ w		
Peak Gate Voltage	(V <sub>GM</sub> ))	10	//v		
Peak Gate Current	IGM	2	A		
Junction Temperature	// )Tj	-40~125			
Storage Temperature Ra	T <sub>stg</sub>	-40~125	°C		
Isolation Voltage (AC, t	⊃ V <sub>ISOL</sub>	1500	V		

Weight: 1.7 g (typ.)

Note 1: di / dt test condition  $V_{DRM} = 0.5 \times Rated$   $I_{TM} \le 4.5A$   $t_{gw} \ge 10 \mu s$ 

 $t_{gr} \le 250 \text{ns}$  $t_{gp} = t_{GT} \times 2.0$ 

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

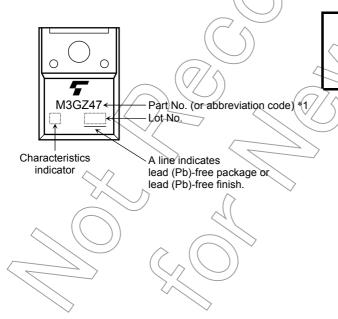
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



## **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT
Repetitive Peak Off-State Current		I <sub>DRM</sub>	V <sub>DRM</sub> = Rated		_	_	20	μΑ
Gate Trigger Voltage	I	V <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 20Ω	T2 (+), Gate (+)	_	-	1.5	- V
	II			T2 (+), Gate (-)	$\nearrow$	_	1.5	
	III			T2 (-), Gate (-)	(-)	4	1.5	
	IV			T2 (-), Gate (+)		) —	-	
Gate Trigger Current	I	lgт	V <sub>D</sub> = 12V R <sub>L</sub> = 20Ω	T2 (+), Gate (+)		_	20	- mA
	II			T2 (+), Gate (-)	<u> </u>	_	20	
	III			T2 (-), Gate (-)	· —	-	20	
	IV			T2 (-), Gate (+)	_	_	_	
Peak On-State Voltage		$V_{TM}$	I <sub>TM</sub> = 4.5A	4	_	4	1,5	V
Gate Non-Trigger Voltage		$V_{GD}$	V <sub>D</sub> = Rated, Tc = 125°C		0.2	1		V
Holding Current		I <sub>H</sub>	V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A		-((		30	mA
Thermal Resistance		R <sub>th (j-c)</sub>	Junction to Case, AC		( <del>-</del>	(4)	4.2	°C/W
Critical Rate of Rise of Off-State Voltage dv / dt		V <sub>DRM</sub> = Rated, T <sub>j</sub> = 125°C Exponential Rise			300	_	V / µs	
Critical Rate of Rise of Off-State Voltage at Commutation		(dv / dt) c	$V_{DRM} = 400V$ , $T_j = 125^{\circ}C$ (di /dt) $c = -2.0A$ / ms		10	ı	1	V / µs

### **MARKING**



Part No.

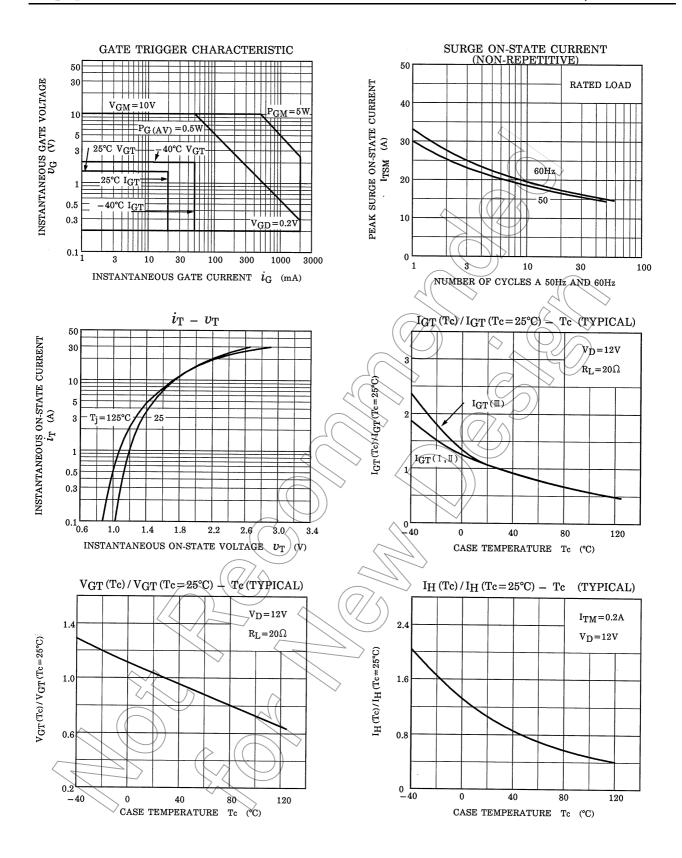
(or abbreviation code) M3GZ47

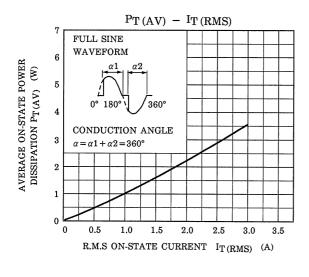
M3JZ47

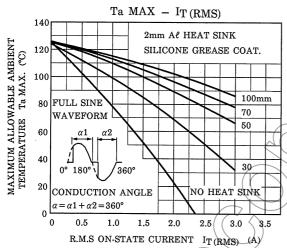
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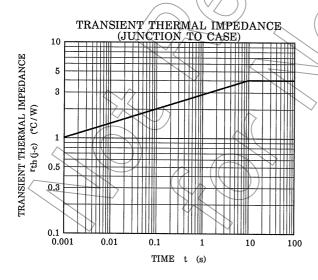
SM3GZ47

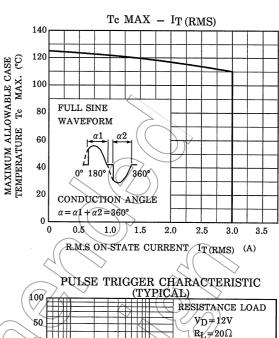
SM3JZ47

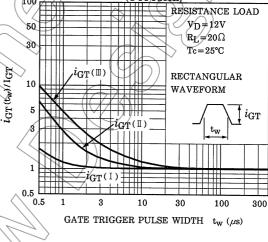












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